



P-CHANNEL ENHANCEMENT MODE MOSFET

Product Summary

BV _{DSS}	RDS(ON) Max	I _D T _A = +25°C
-40V	11mΩ @ V _{GS} = -10V	-11.4A
	15mΩ @ V _{GS} = -4.5V	-9.8A

Description and Applications

This MOSFET is designed to meet the stringent requirements of Automotive applications. It is qualified to AEC-Q101, supported by a PPAP and is ideal for use in:

- DC-DC Converters
- Power Management Functions
- Analog Switch

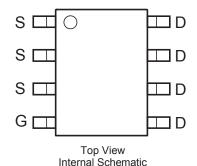
Features and Benefits

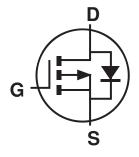
- Rated to +175°C Ideal for High Ambient Temperature Environments
- 100% Unclamped Inductive Switch (UIS) Test in Production Low On-Resistance
- · Low Input Capacitance
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability
- PPAP Capable (Note 4)

Mechanical Data

- Case: SO-8
- Case Material: Molded Plastic, "Green" Molding Compound.
 UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Connections: See Diagram
- Terminals: Finish Matte Tin Annealed over Copper Leadframe.
 Solderable per MIL-STD-202, Method 208 (§3)
- Weight: 0.074 grams (Approximate)







Equivalent Circuit

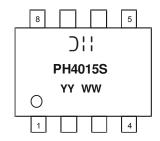
Ordering Information (Note 5)

Part Number	Case	Packaging
DMPH4015SSSQ-13	SO-8	2,500/Tape & Reel

Notes:

- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.
- See http://www.diodes.com/quality/lead_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. Automotive products are AEC-Q101 qualified and are PPAP capable. Refer to http://www.diodes.com/product_compliance_definitions.html.
- 5. For packaging details, go to our website at http://www.diodes.com/products/packages.html.

Marking Information



);; = Manufacturer's Marking
PH4015S = Product Type Marking Code
YYWW = Date Code Marking
YY = Year (ex: 16 = 2016)
WW = Week (01 to 53)



Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic			Symbol	Value	Unit
Drain-Source Voltage			V _{DSS}	-40	V
Gate-Source Voltage			V _{GSS}	±25	V
Continuous Drain Current (Note 7) V _{GS} = -10V	Steady State	$T_A = +25^{\circ}C$ $T_A = +100^{\circ}C$	I _D	-11.4 -8.1	А
Pulsed Drain Current (10µs Pulse, Duty Cycle = 1%)			I _{DM}	-85	Α
Maximum Body Diode Continuous Current (Note 7)			Is	-3	Α
Avalanche Current (Note 8) L = 1mH			I _{AS}	-22	Α
Avalanche Energy (Note 8) L = 1mH			Eas	260	mJ

Thermal Characteristics

Characteristic	Symbol	Value	Unit
Total Power Dissipation (Note 6)	P _D	1.4	W
Thermal Resistance, Junction to Ambient (Note 6)	R _{θJA}	90	°C/W
Total Power Dissipation (Note 7)	P _D	1.8	W
Thermal Resistance, Junction to Ambient (Note 7)	Reja	70	°C/W
Thermal Resistance, Junction to Case (Note 7)	R _{eJC}	7.0	°C/W
Operating and Storage Temperature Range	T _J , T _{STG}	-55 to +175	°C

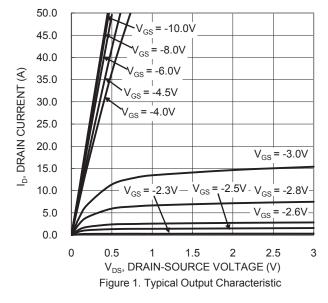
Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

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Characteristic (A)	Symbol	Min	Тур	Max	Unit	Test Condition	
OFF CHARACTERISTICS (Note 9)	1		1	1			
Drain-Source Breakdown Voltage	BV _{DSS}	-40			V	$V_{GS} = 0V, I_D = -250\mu A$	
Zero Gate Voltage Drain Current	I _{DSS}	_	_	-1	μΑ	V_{DS} = -40V, V_{GS} = 0V	
Gate-Source Leakage	I _{GSS}	_	—	±100	nA	$V_{GS} = \pm 25V, V_{DS} = 0V$	
ON CHARACTERISTICS (Note 9)							
Gate Threshold Voltage	V _{GS(TH)}	-1.5	_	-2.5	V	$V_{DS} = V_{GS}, I_{D} = -250 \mu A$	
Static Drain-Source On-Resistance		_	9	11	mΩ	$V_{GS} = -10V, I_D = -9.8A$	
Static Drain-Source On-Resistance	R _{DS(ON)}	_	11	15	11177	$V_{GS} = -4.5V$, $I_D = -9.8A$	
Forward Transfer Admittance	Y _{fs}	_	26	_	S	V _{DS} = -20V, I _D = -9.8A	
Diode Forward Voltage	V _{SD}	_	-0.7	-1	V	V _{GS} = 0V, I _S = -1A	
DYNAMIC CHARACTERISTICS (Note 10)			•		•		
Input Capacitance	C _{iss}	_	4,234	_		V _{DS} = -20V, V _{GS} = 0V f = 1MHz	
Output Capacitance	Coss	_	1,036	_	pF		
Reverse Transfer Capacitance	C _{rss}	_	526	_			
Gate Resistance	R _G	_	7.8	_	Ω	$V_{DS} = 0V$, $V_{GS} = 0V$, $f = 1MHz$	
Total Gate Charge (V _{GS} = -4.5V)	Qg	_	42.7	_		V _{DS} = -20V, I _D = -9.8A	
Total Gate Charge (V _{GS} = -10V)	Qg	_	91	_	nC		
Gate-Source Charge	Qgs	_	14.2	_	IIC		
Gate-Drain Charge	Q_{gd}	_	13.5	_			
Turn-On Delay Time	t _{D(ON)}	_	13.2	_		V_{GS} = -10V, V_{DD} = -20V, R_{G} = 6 Ω , I_{D} = -1A, R_{L} = 20 Ω	
Turn-On Rise Time	t _R	_	10	_			
Turn-Off Delay Time	t _{D(OFF)}	_	303	_	ns		
Turn-Off Fall Time	t _F	_	138	_			
Reverse Recovery Time	t _{RR}	_	26	_	ns	I _F = -9.8A, di/dt = -100A/μs	
Reverse Recovery Charge	Q _{RR}	_	20	_	nC	I _F = -9.8A, di/dt = -100A/µs	

Notes

- 6. Device mounted on FR-4 PC board, with minimum recommended pad layout, single sided.
- 7. Device mounted on FR-4 substrate PC board, 2oz copper, with thermal bias to bottom layer 1inch square copper plate.
- 8. I_{AS} and E_{AS} ratings are based on low frequency and duty cycles to keep T_J = +25°C.
- 9. Short duration pulse test used to minimize self-heating effect.
- 10. Guaranteed by design. Not subject to product testing.





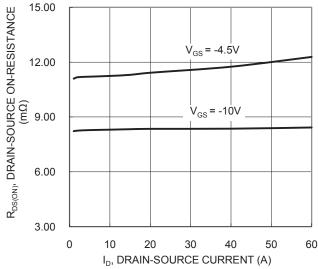


Figure 3. Typical On-Resistance vs. Drain Current and Gate Voltage

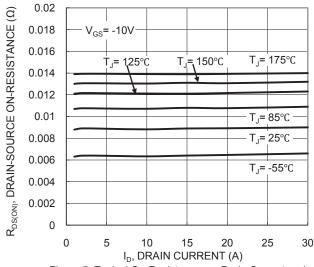
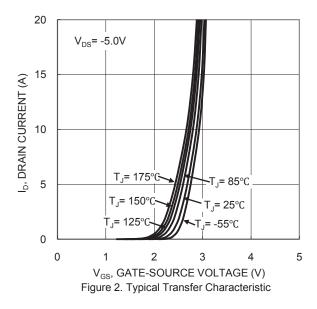
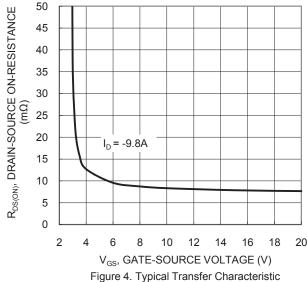


Figure 5. Typical On-Resistance vs. Drain Current and Temperature





2.2 R_{DS(ON)}, DRAIN-SOURCE ON-RESISTANCE (NORMALIZED) 2 1.8 $V_{GS} = -10V, I_D = -9_8A$ 1.6 1.4 1.2 $V_{GS} = -4.5V, I_{D} = -9.8A$ 1 8.0 0.6 0.4 0 75 100 125 150 175 -50 -25 25 50 T_{.I}, JUNCTION TEMPERATURE (°C)

Figure 6. On-Resistance Variation with Temperature



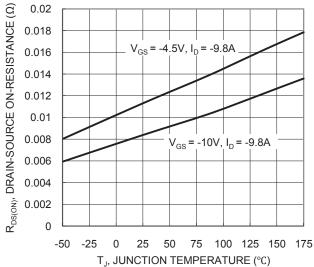
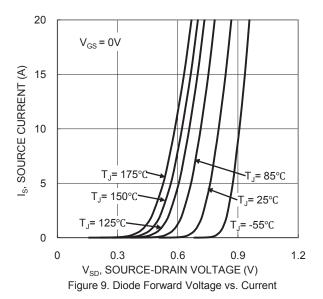
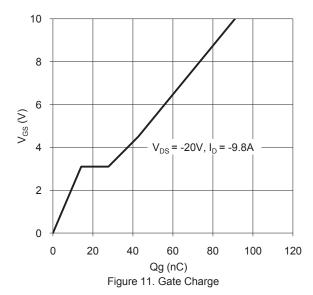


Figure 7. On-Resistance Variation with Temperature





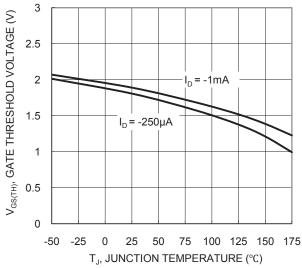
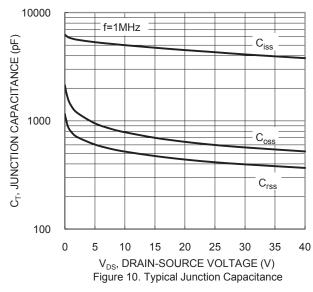
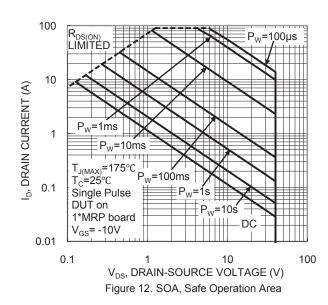


Figure 8. Gate Threshold Variation vs. Junction Temperature







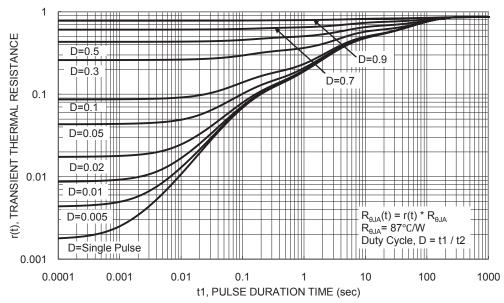


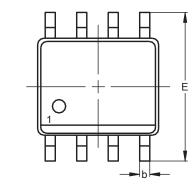
Figure 13. Transient Thermal Resistance

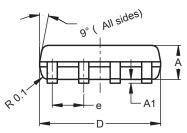


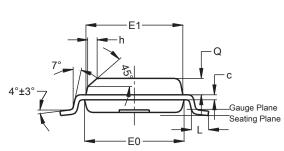
Package Outline Dimensions

Please see http://www.diodes.com/package-outlines.html for the latest version.

SO-8



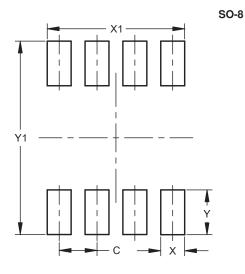




SO-8				
Dim	Min	Max	Тур	
Α	1.40	1.50	1.45	
A 1	0.10	0.20	0.15	
b	0.30	0.50	0.40	
С	0.15	0.25	0.20	
D	4.85	4.95	4.90	
Е	5.90	6.10	6.00	
E1	3.80	3.90	3.85	
E0	3.85	3.95	3.90	
е			1.27	
h	-		0.35	
Г	0.62	0.82	0.72	
Q	0.60	0.70	0.65	
All Dimensions in mm				

Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.



Dimensions	Value (in mm)			
С	1.27			
Х	0.802			
X1	4.612			
Υ	1.505			
Y1	6.50			



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